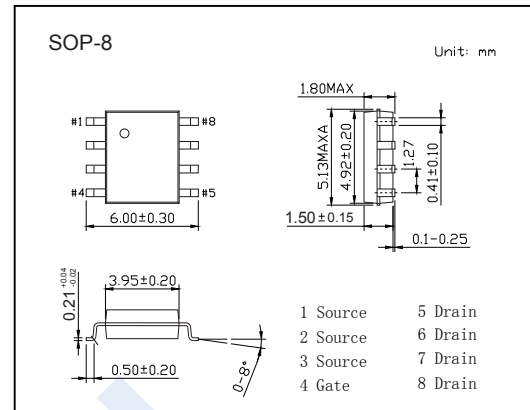
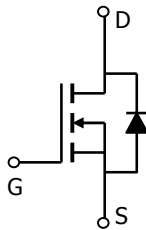


N-Channel MOSFET

AO4410 (KO4410)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 18 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 5.5m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 6.2m\Omega$ ($V_{GS} = 4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	±12	
Continuous Drain Current	TA=25℃	I _D	18	A
	TA=70℃		15	
Pulsed Drain Current		I _{DM}	80	
Power Dissipation	TA=25℃	P _D	3.1	W
	TA=70℃		2	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R _{thJA}	40	℃/W
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R _{thJL}	24	
Junction Temperature		T _J	150	℃
Storage Temperature Range		T _{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 uA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.8		1.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =18A			5.5	mΩ
		V _{GS} =10V, I _D =18A T _J =125°C			7.4	
		V _{GS} =4.5V, I _D =15A			6.2	
On State Drain Current	I _{D(ON)}	V _{GS} =4.5V, V _{DS} =5V	80			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =18A		102		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz		9130	10500	pF
Output Capacitance	C _{oss}			625		
Reverse Transfer Capacitance	C _{rss}			387		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.4	0.5	Ω
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =18A		72.4	85	nC
Gate Source Charge	Q _{gs}			13.4		
Gate Drain Charge	Q _{gd}			16.8		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _L =0.83Ω, R _{GEN} =3Ω		11	15	ns
Turn-On Rise Time	t _r			7	11	
Turn-Off DelayTime	t _{d(off)}			99	135	
Turn-Off Fall Time	t _f			13	19.5	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 18A, di/dt= 100A/us		33	40	nC
Body Diode Reverse Recovery Charge	Q _{rr}			22.2	30	
Maximum Body-Diode Continuous Current	I _S				4.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4410 KC****
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N-Channel MOSFET

AO4410 (KO4410)

■ Typical Characteristics

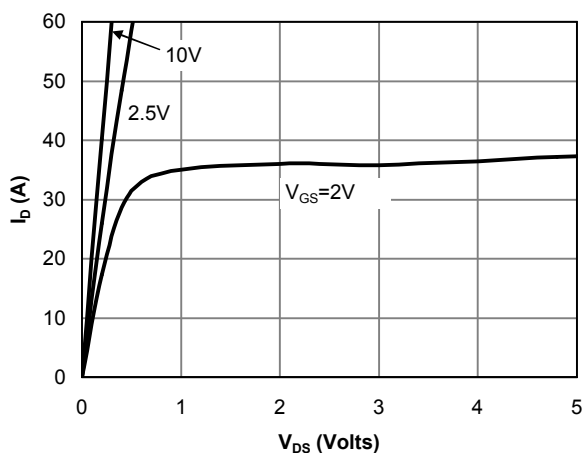


Fig 1: On-Region Characteristics

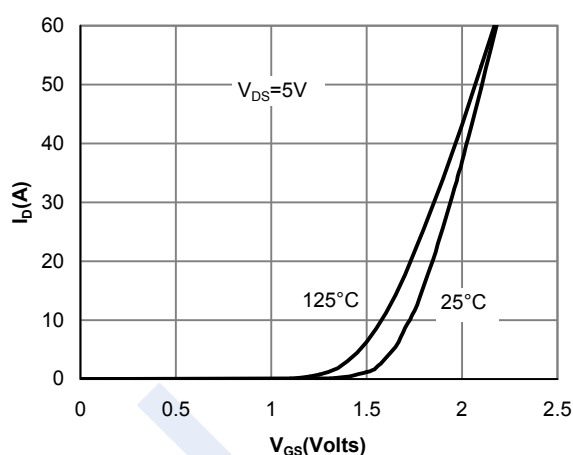


Figure 2: Transfer Characteristics

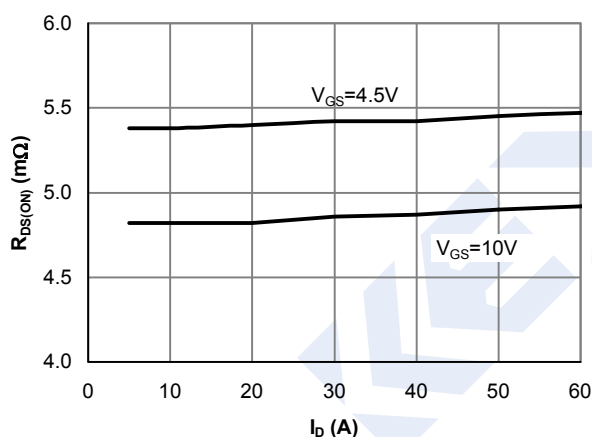


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

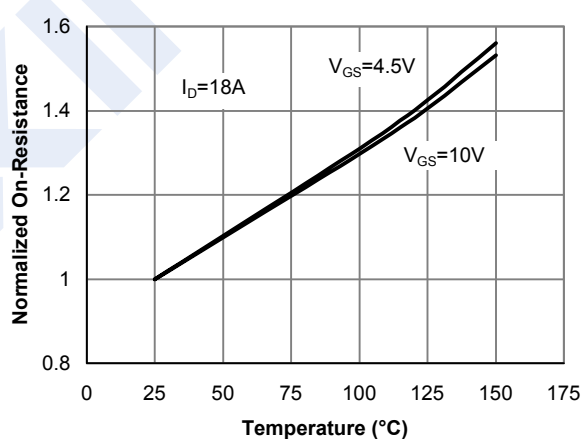


Figure 4: On-Resistance vs. Junction Temperature

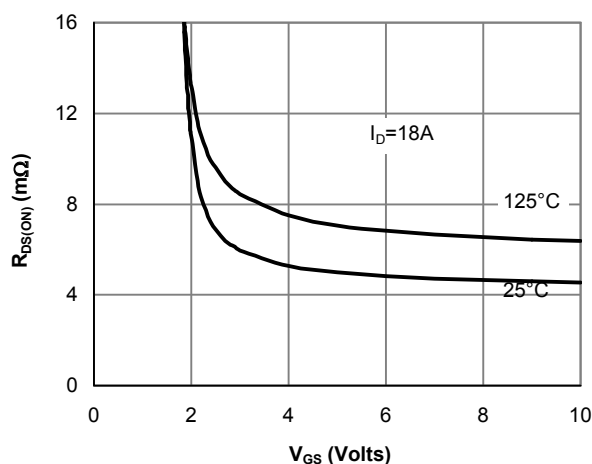


Figure 5: On-Resistance vs. Gate-Source Voltage

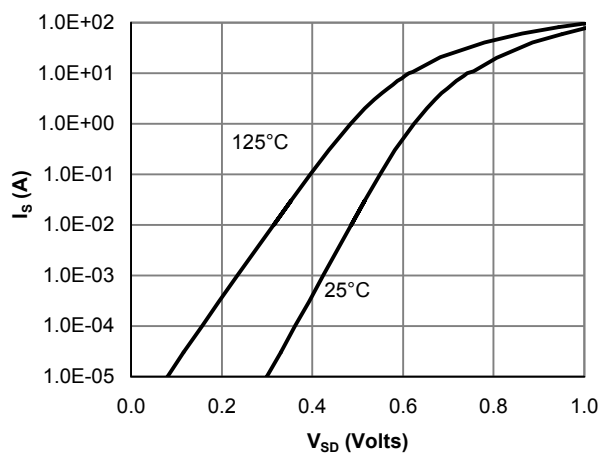


Figure 6: Body-Diode Characteristics

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■ Typical Characteristics

